

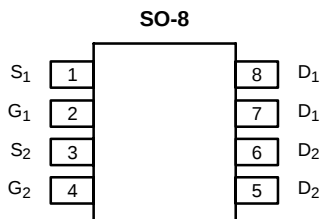


Dual N-Channel 30-V (D-S) MOSFET with Schottky Diode

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
30	0.022 @ $V_{GS} = 10$ V	7.5
	0.030 @ $V_{GS} = 4.5$ V	6.5

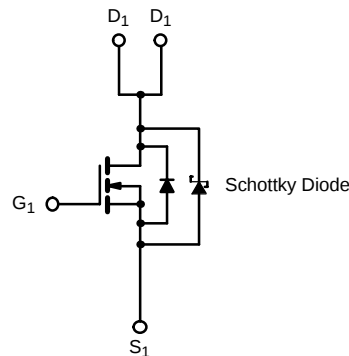
SCHOTTKY PRODUCT SUMMARY		
V_{DS} (V)	V_{SD} (V) Diode Forward Voltage	I_F (A)
30	0.50 V @ 1.0 A	2.0

LITTLE FOOT PLUS™

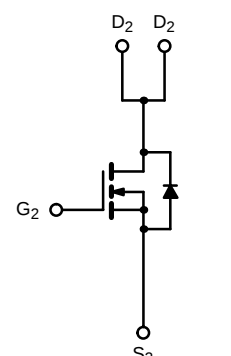


Top View

Ordering Information: Si4834DY
Si4834DY-T1 (with Tape and Reel)



N-Channel MOSFET



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)				
Parameter		Symbol	10 secs	Steady State
Drain-Source Voltage		V_{DS}	30	
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current ($T_J = 150^\circ\text{C}$) ^a	$T_A = 25^\circ\text{C}$	I_D	7.5	5.7
	$T_A = 70^\circ\text{C}$		6.0	4.6
Pulsed Drain Current		I_{DM}	30	
Continuous Source Current (Diode Conduction) ^a		I_S	1.7	0.9
Maximum Power Dissipation ^a	$T_A = 25^\circ\text{C}$	P_D	2.0	1.1
	$T_A = 70^\circ\text{C}$		1.3	0.7
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150	

THERMAL RESISTANCE RATINGS							
Parameter		Symbol	MOSFET		Schottky		Unit
			Typ	Max	Typ	Max	
Maximum Junction-to-Ambient ^a	$t \leq 10$ sec	R_{thJA}	52	62.5	53	62.5	$^\circ\text{C/W}$
	Steady-State		93	110	93	110	
Maximum Junction-to-Foot (Drain)	Steady-State	R_{thJC}	35	40	35	40	

Notes

a. Surface Mounted on 1" x 1" FR4 Board.

MOSFET SPECIFICATIONS (T _J = 25° C UNLESS OTHERWISE NOTED).							
Parameter	Symbol	Test Condition		Min	Typ ^a	Max	Unit
Static							
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		0.8			V
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V				± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 24 V, V _{GS} = 0 V	Ch-1			100	μA
			Ch-2			1	
		V _{DS} = 24 V, V _{GS} = 0 V, T _J = 85°C	Ch-1			2000	
			Ch-2			15	
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V		20			A
Drain-Source On-State Resistance ^b	r _{DS(on)}	V _{GS} = 10 V, I _D = 7.5 A			0.018	0.022	Ω
		V _{GS} = 4.5 V, I _D = 6.5 A			0.024	0.030	
Forward Transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 7.5 A			22		S
Diode Forward Voltage ^b	V _{SD}	I _S = 1 A, V _{GS} = 0 V	Ch-1		0.47	0.5	V
			Ch-2		0.8	1.2	
Dynamic ^a							
Total Gate Charge	Q _g	V _{DS} = 15 V, V _{GS} = 10 V, I _D = 7.5 A			13	20	nC
Gate-Source Charge	Q _{gs}				2		
Gate-Drain Charge	Q _{gd}				2.7		
Gate Resistance	R _g			0.5	1.9	3.2	Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = 15 V, R _L = 15 Ω I _D ≅ 1 A, V _{GEN} = 10 V, R _G = 6 Ω			8	16	ns
Rise Time	t _r				10	20	
Turn-Off Delay Time	t _{d(off)}				21	40	
Fall Time	t _f				10	20	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 1.7 A, di/dt = 100 A/μs	Ch-1		32	70	
			Ch-2		40	80	

Notes

- a. Guaranteed by design, not subject to production testing.
b. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.

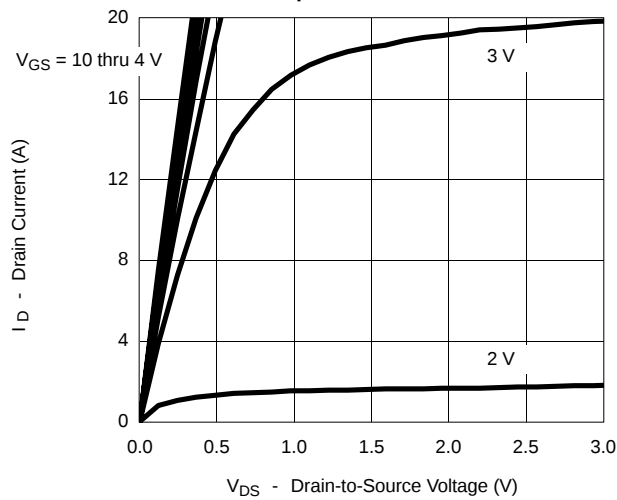
SCHOTTKY SPECIFICATIONS ($T_J = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Forward Voltage Drop	V_F	$I_F = 1.0\ \text{A}$		0.47	0.50	V
		$I_F = 1.0\ \text{A}$, $T_J = 125^\circ\text{C}$		0.36	0.42	
Maximum Reverse Leakage Current	I_{rm}	$V_r = 30\ \text{V}$		0.004	0.100	mA
		$V_r = 30\ \text{V}$, $T_J = 100^\circ\text{C}$		0.7	10	
		$V_r = -30\ \text{V}$, $T_J = 125^\circ\text{C}$		3.0	20	
Junction Capacitance	C_T	$V_r = 10\ \text{V}$		50		pF



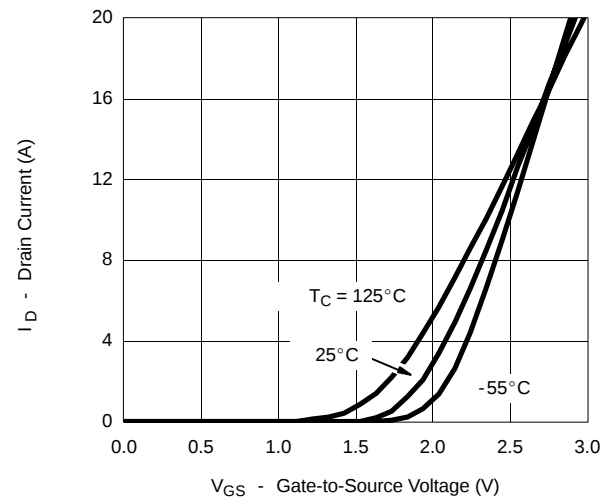
TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

MOSFET

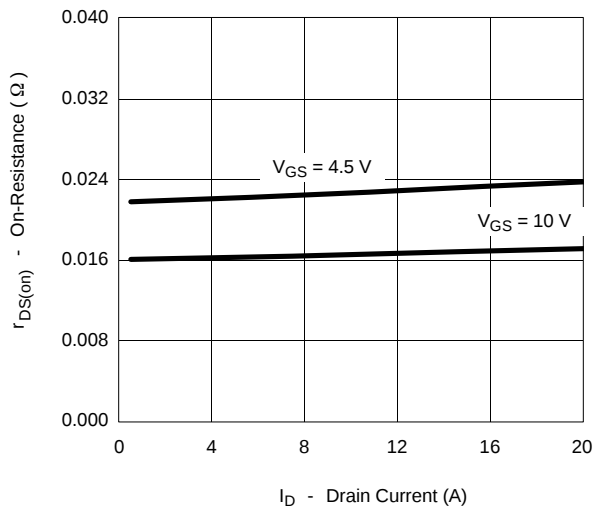
Output Characteristics



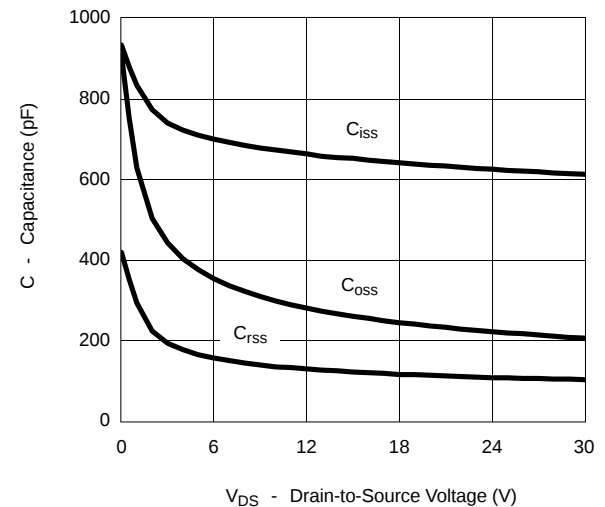
Transfer Characteristics



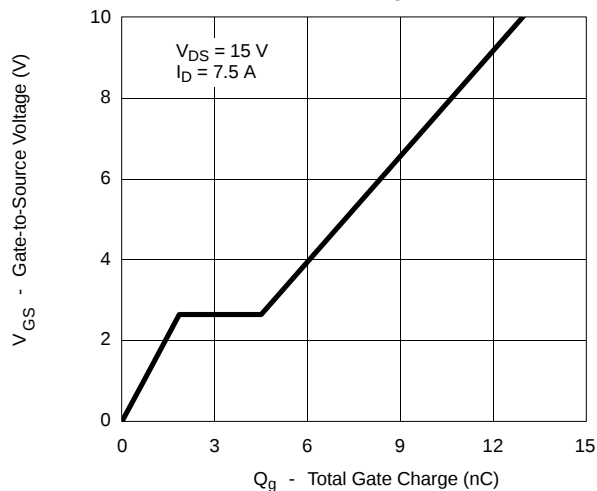
On-Resistance vs. Drain Current



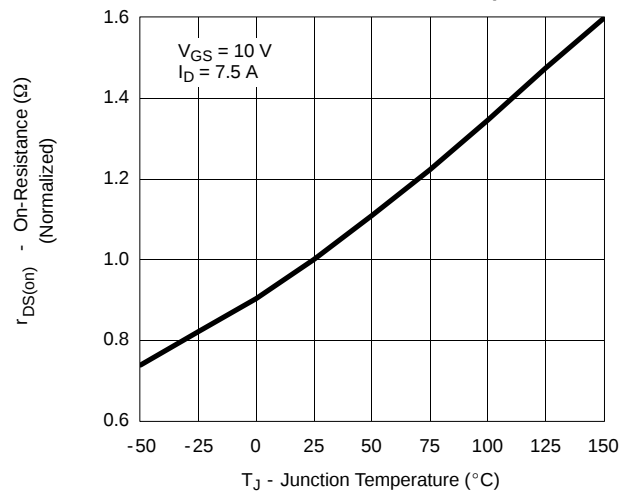
Capacitance



Gate Charge

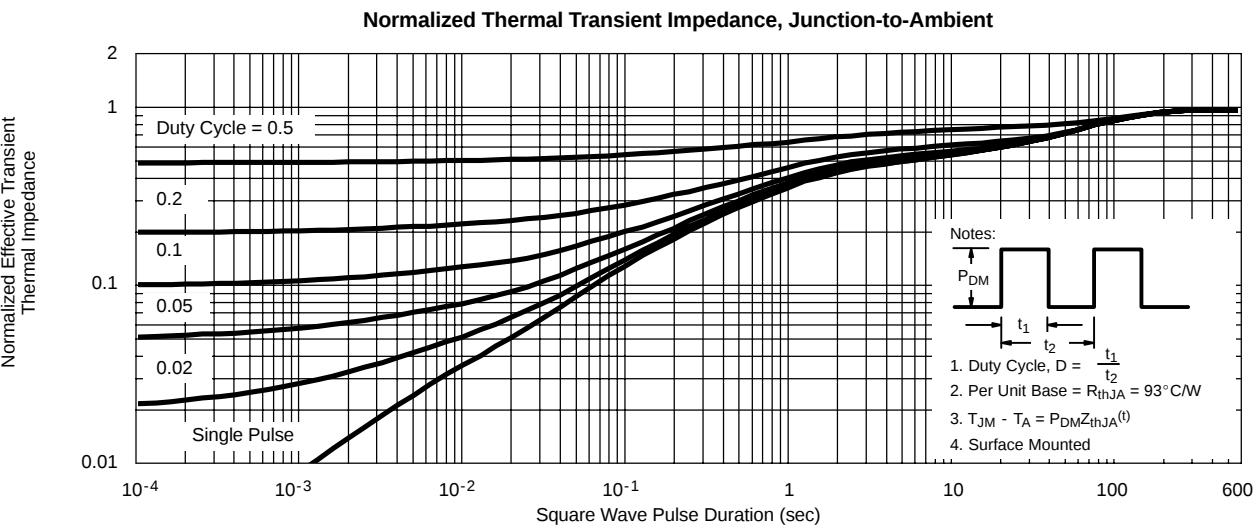
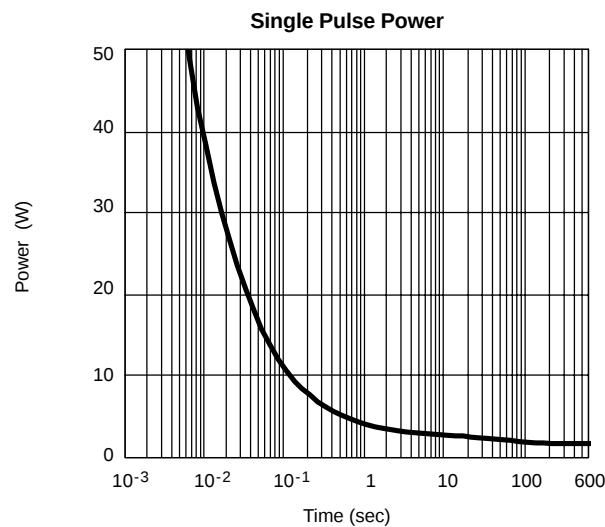
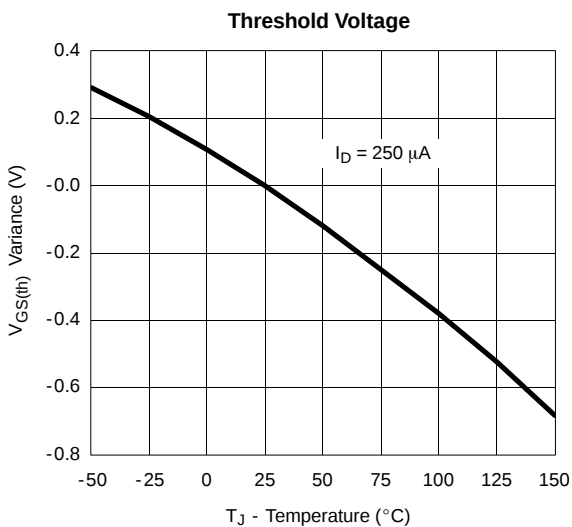
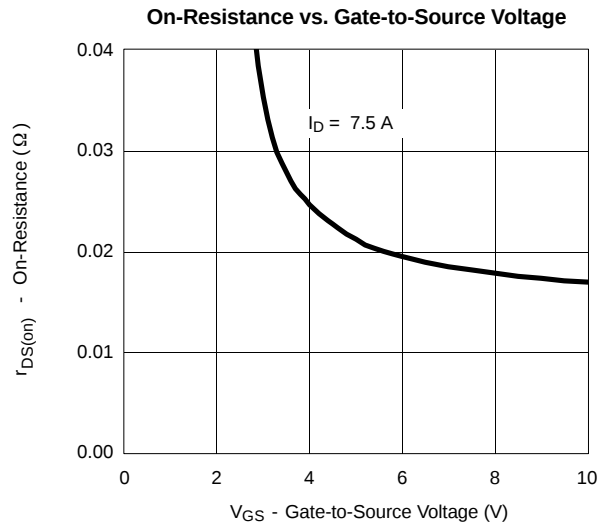
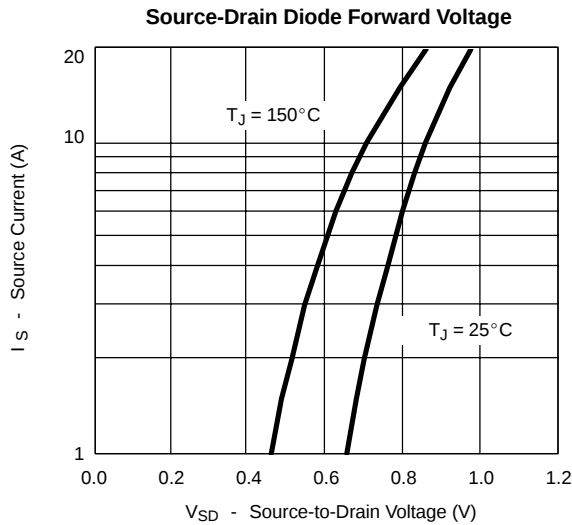


On-Resistance vs. Junction Temperature





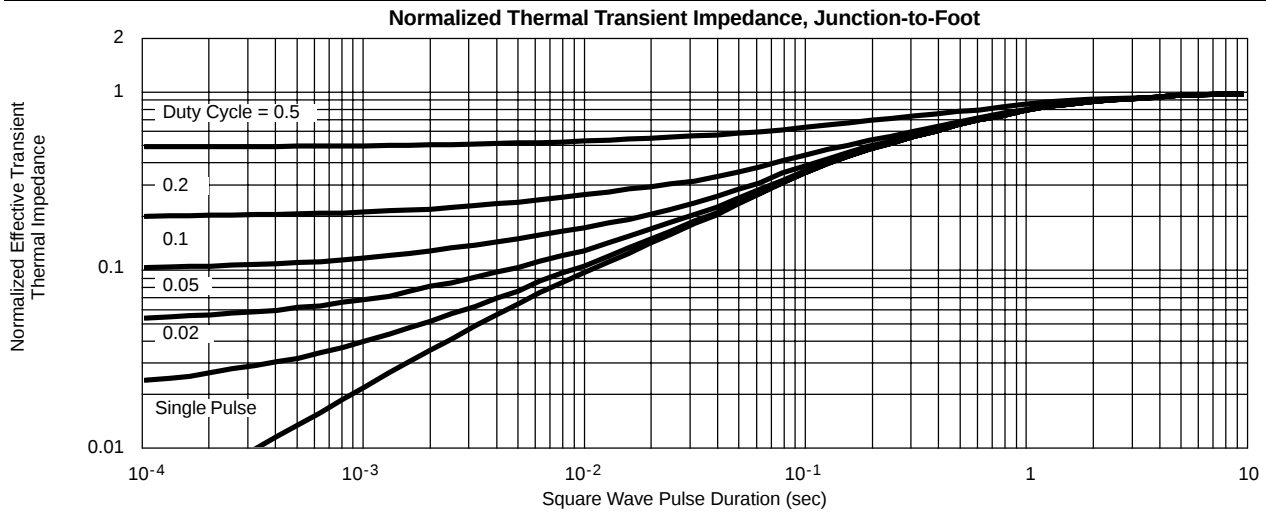
TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED) **MOSFET**





TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

MOSFET



TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

SCHOTTKY

